35K 192

Silicon N Channel 4-pole MOS Type

For VHF/UHF band high-gain low-noise amplification

Features

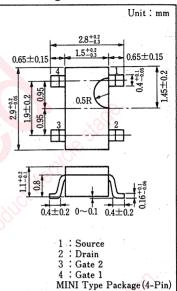
- •Low noise figure NF
- •Large power gain PG
- •A MINI type package that allows downsizing of equipment and automatic insertion by taping and magazine packaging

■ Absolute Maximum Ratings (Ta=25°C)

Item 1	Symbol	Value	Unit
Drain-Source Voltage	V _{DS}	15	V
Gate 1-Source Voltage	V _{G1S}	±8	V
Gate 2-Source Voltage	V _{G2S}	±8	v
Drain Current	I_{D}	30	mA
Power Dissipation	P _D	150	mW
Channel Temperature	Tch	150	C
Storage Temperature	T _{stg}	-55~+150	C 60

■ Electrical Characteristics (Ta=25°C)

■ Package Dimensions



Item	Symbol	Condition	min.	typ.	max.	Unit
Drain-Source Voltage	V _{DSX}	$I_D = 50 \mu A$, $V_{G1S} = -5 V$, $V_{G2S} = 0$	1.5		6, 0	V
Drain Current	I _{DSS} *	$V_{DD} = 10V$, $V_{G1S} = 0$, $V_{G2S} = 4V$	1.5		10	m A
Gate 1-Source Cutoff Current	V _{G1SC}	$V_{DS} = 10V$, $V_{G2S} = 4 V$, $I_{D} = 100 \mu A$	-3.0	100	+0.5	V
Gate 2-Source Cut off Current	V_{G2SC}	$V_{DS} = 10V$, $V_{G1S} = 4 V$, $I_{D} = 100 \mu A$	-1.5	· (C)	+1.5	V
Gate 1 Cutoff Current	I _{G1SS}	$V_{G1S} = \pm 8 \text{ V}, \ V_{DS} = V_{G2S} = 0$	70,	-0/1	+2.0	nA
Gate 2 Cutoff Current	I _{G2SS}	$V_{G2S} = \pm 8 \text{ V}, V_{DS} = V_{G1S} = 0$	37 13	,	+2.0	nΑ
Forward Transfer Admittance (Common Source)	Yfs	$V_{DS}=10V$, $V_{G2S}=4V$, $I_{D}=10mA$, $f=1 \text{ kHz}$	18	26	34	mS
Input Capacitance	Ciss	$V_{DS} = 10V$, $V_{G1S} = V_{G2S} = -5 V$, $f = 1 MHz$	1.7	2.7		pF
Output Capacitance	Coss	$V_{DS} = 10V$, $V_{G1S} = V_{G2S} = -5V$, $f = 1MHz$)	1.1	1.7	pF
Small-Signal Reverse Transfer Capacitance	C _{rss}	$V_{DS} = 10V$, $V_{GS} = V_{G2S} = -5V$, $f = 1 \text{ MHz}$		0.02	1	. pF
Power Gain	PG ₁ *1	$V_{DS} = 8 \text{ V}, V_{G2S} = 3 \text{ V}, I_D = 8 \text{ mA}$	22	24	1. 1. 1. 1. 1.	dB
Noise Figure	NF ₁ *1	f=50~60MHz (SWEEP)		2.4	3.2	dB
Power Gain	PG ₂ *2	$V_{DS} = 8 \text{ V}, V_{G2S} = 3 \text{ V}, I_D = 8 \text{ mA}$	22	24		dB
Noise Figure	NF ₂ *2	f=190~210MHz (SWEEP)		1.5	2.5	dB
Power Gain	PG ₃ *3	$V_{DS} = 8 \text{ V}, V_{G2S} = 3 \text{ V}, I_D = 8 \text{ mA}$	14.5	17		dB
Noise Figure	NF ₃ *3	f=490~510MHz (SWEEP)		2.8	4.5	dB

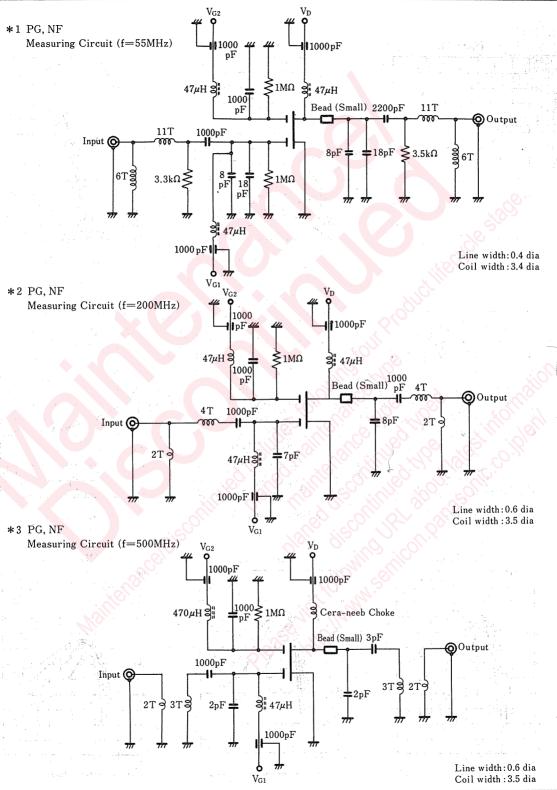
*Inss Ranking

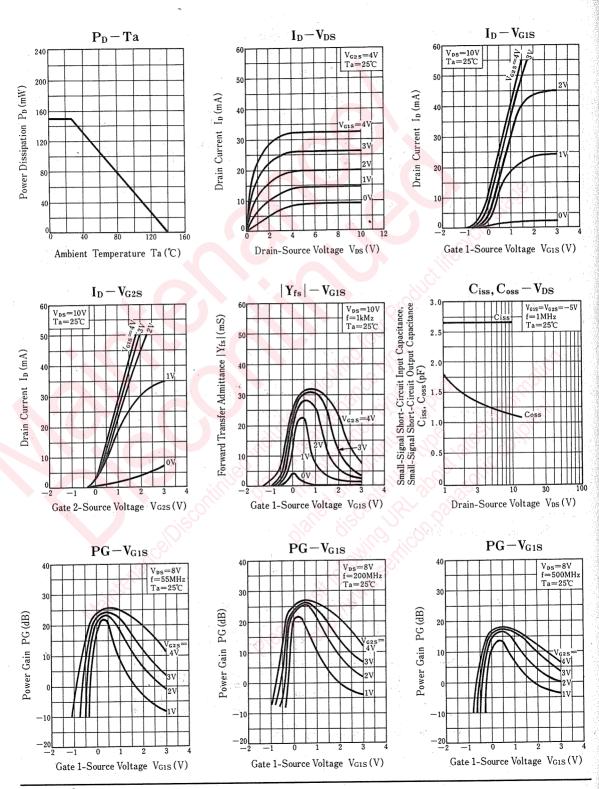
Rank	P	Q
I _{DSS} (mA)	1~5	4~12
Marking	3XP	3XQ

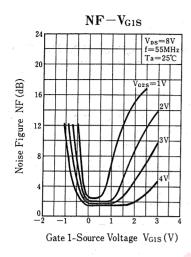
■ Type Name Marking (Example)

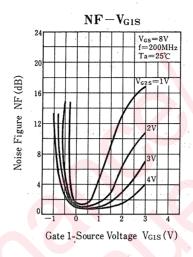
Type No. IDSS Ranking

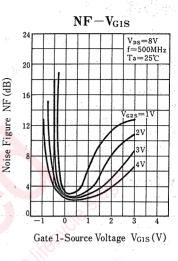


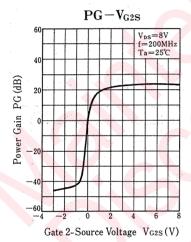


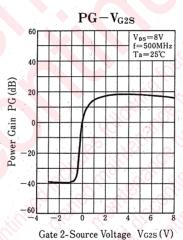


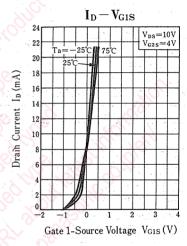












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